

# DESIGN OF RF FILTER BASED ON RF COMPONENTS

NORSHAKILA BINTI HARIS

A project report submitted in partial fulfilment of the  
requirements for the award of the degree of  
Master of Engineering (Electrical – Electronic & Telecommunication)

Faculty of Electrical Engineering  
Universiti Teknologi Malaysia

MAY 2008

Thanks to Allah for all the blessing in accomplishing this thesis. I dedicate this work to my beloved mother and father for their infinite love, patience and encouragement that helped me to accomplish this course of work successfully.

## **ACKNOWLEDGEMENT**

I wish to extend my gratefulness to Assoc. Prof. Dr. Mazlina Esa for her full supervision throughout the course and her generosity of proposing many great ideas towards the making of this project.

I would also like to thanks my friends at UTM for their support and encouragement.

Finally, I deeply thank my family members; my mother, my father, my sisters and my little brother for giving me their love and tremendous support.

Thank you all.

## ABSTRACT

Inductors, L, and capacitors, C, are among the most important circuit elements, especially for the radio frequency, RF, applications. Such applications of these components include frequency-tuning circuits, filters, mixers, and matching networks. This thesis presents the design and modelling of RF filters that consist of on-chip RF components. Firstly, two on-chip RF components have been separately designed before they were formed into an RF filter. The chosen configurations are the interdigital capacitor and spiral inductor. The effects of parameter variations on quality factor and inductance or capacitance values were investigated using simulation software. Upon achieving the desired performances, the components were arranged into series and shunt, forming two corresponding filter configurations. Both configurations were then connected to form a single stage series-shunt LC filter using parallel connection. Simulation results showed that both components operate well at the desired 13 GHz RF frequency of operation. The series and shunt LC filters demonstrate characteristics of a bandpass filter. At -3 dB or half-power insertion and return losses, both exhibit operating bandwidths from 8 GHz to 11 GHz, i.e. 3.0 GHz or 32 %. In ratio form, this is  $11/8 = 1.375$  which is quite broad. The single stage series-shunt LC filter also demonstrates characteristics of a bandpass filter. It exhibits slightly less -3 dB operating bandwidth from 8.75 GHz to 10.25 GHz, i.e. 1.5 GHz or 16 %. In ratio form, this is  $10.25/8.75 = 1.17$  which is slightly broad. This is halved that of the series and shunt LC filters. Hence, the former exhibits a maximum Q factor of approximately 3.2, which is doubled that of the single stage series-shunt LC filter.

## ABSTRAK

Induktor, L, dan kapasitor, C, merupakan antara elemen terpenting litar, terutamanya bagi aplikasi frekuensi radio, RF. Contoh aplikasi termasuklah litar menala-frekuensi, penapis, pencampur, dan rangkaian padanan. Tesis ini membentangkan rekabentuk dan pemodelan penapis RF yang terdiri daripada komponen *on-chip* RF. Pertamanya, dua komponen RF direkabentuk secara berasingan terlebih dahulu sebelum digabung menjadi struktur penapis. Konfigurasi yang dipilih adalah kapasitor salingdigital dan induktor pilin. Pengaruh perubahan parameter terhadap faktor kualiti dan nilai aruhan atau muatan telah diselidik menggunakan perisian simulasi. Setelah prestasi yang dikehendaki diperoleh, komponen ini disambung secara siri dan selari untuk membentuk dua konfigurasi penapis sehubungan. Kedua-dua konfigurasi kemudiannya disambung membentuk penapis LC siri-selari peringkat tunggal. Keputusan simulasi menunjukkan bahawa kedua-dua komponen berkendali dengan baik pada frekuensi 13 GHz yang dikehendaki. Penapis LC siri dan selari telah berjaya mempamerkan ciri penapis lulus jalur. Pada paras -3 dB atau kehilangan sisipan dan kembali setengah-kuasa, kedua-duanya memiliki lebarjalur kendalian dari 8 GHz hingga 11 GHz, i.i. 3.0 GHz atau 32 %. Dalam bentuk nisbah, ini ialah  $11/8 = 1.375$  iaitu agak luas. Penapis LC siri-selari peringkat tunggal telah juga mempamerkan ciri penapis lulus jalur. Ia memiliki lebarjalur kendalian yang kurang sedikit, iaitu dari 8.75 GHz hingga 10.25 GHz, i.i. 1.5 GHz atau 16 %. Dalam bentuk nisbah, ini ialah  $10.25/8.75 = 1.17$  iaitu luas sedikit. Ini ialah separuh daripada keluasan lebarjalur litar LC siri dan selari. Oleh itu, litar pertama memiliki faktor Q maksimum bernilai hampir 3.2, iaitu dua kali ganda pada penapis LC siri-selari peringkat tunggal.

## TABLE OF CONTENTS

CHAPTER	TITLE	PAGE
	<b>DECLARATION</b>	ii
	<b>DEDICATION</b>	iii
	<b>ACKNOWLEDGEMENT</b>	iv
	<b>ABSTRACT</b>	v
	<b>ABSTRAK</b>	vi
	<b>TABLE OF CONTENTS</b>	vii
	<b>LIST OF TABLES</b>	x
	<b>LIST OF FIGURES</b>	xi
	<b>LIST OF SYMBOLS</b>	xiii
	<b>LIST OF ABBREVIATIONS</b>	xv
	<b>LIST OF APPENDICES</b>	xvi
<b>1</b>	<b>INTRODUCTION</b>	1
	1.1 Project Background	1
	1.2 Objective of Project	2
	1.3 Scopes of Project	3
	1.4 Organization of Thesis	3
<b>2</b>	<b>REVIEW OF RF LUMPED ELEMENTS, RF FILTERS AND BRIEF THEORIES</b>	5
	2.1 Introduction	5
	2.2 Passive Microwave Lumped Elements	5
	2.2.1 Interdigital Capacitors	6
	(a) Capacitance, C	8

	(b)	Quality Factor, Q	10
	(c)	Series Resistance	10
	(d)	Characteristic Impedance	11
	2.2.2	Spiral Inductors	12
	(a)	Inductance, L	14
	(b)	Quality Factor, Q	15
	(c)	Series Resistance	16
	(d)	Characteristic Impedance	17
2.3		LC Filters	18
	2.3.1	Bandwidth	22
	2.3.2	Quality Factor	22
<b>3</b>		<b>DESIGN METHODOLOGY AND SOFTWARE</b>	
		<b>DESCRIPTIONS</b>	24
	3.1	Introduction	24
	3.2	Overall Project Flow	24
	3.3	Design Specifications	26
	3.4	Software Used	27
	3.4.1	Sonnet Lite	27
	3.4.2	MathCAD	28
<b>4</b>		<b>RESULTS &amp; ANALYSIS</b>	29
	4.1	Introduction	29
	4.2	Initial Designs	29
	4.3	Analysis of Interdigital Capacitors	30
	4.3.1	Design Comparison	32
	4.3.2	Number of Fingers	34
	4.3.3	Finger Length	35
	4.3.4	Types of Metal	37
	4.4	Analysis of Spiral Inductors	38
	4.4.1	Number of Turns	38
	4.4.2	Line Width	40
	4.4.3	Metal Material	41
	4.5	The Optimized C and L	43

4.6	Analysis of LC Filters	45
4.6.1	Series LC Filter and Shunt LC Filter	45
4.6.2	Single-Stage Series-Shunt LC Filter	46
4.6.3	Summary of LC Filters	48
<b>5</b>	<b>CONCLUSION</b>	49
5.1	Conclusion	49
5.2	Future Work	49
	<b>REFERENCES</b>	51
	Appendices A-E	54 - 65



**LIST OF TABLES**

<b>TABLE NO.</b>	<b>TITLE</b>	<b>PAGE</b>
3.1	Design specification of interdigital capacitor	26
3.2	Design specification of spiral inductor	27
4.1	Suitable combination values of number of fingers and finger length	31
4.2	Design geometries of the interdigital capacitor	32
4.3	Q <sub>max</sub> and C values of different designs based on figure 4.3	32
4.4	Q <sub>max</sub> value of different types of metal	37
4.5	The summary of LC filters responses	48

## LIST OF FIGURES

FIGURE NO.	TITLE	PAGE
1.1	An interdigital capacitor configuration	2
1.2	A spiral inductor configuration	2
2.1	Configuration and lumped physical model of interdigital capacitor	7
2.2	Impedance characteristic of a practical capacitor	7
2.3	Finger capacitance contribution as a function of substrate thickness	9
2.4	Configuration and lumped physical model of spiral inductor	13
2.5	Impedance characteristic of inductor	13
2.6	Inductor impedance versus frequency	14
2.7	The Q variation of an inductor with frequency	16
2.8	Parallel and series resonant circuits	20
2.9	Band-pass and band-reject frequency responses	21
2.10	Effect of Q on the bandwidth	23
2.11	The resonant frequency depending of the C and L	23
3.1	First stage of project flow	25
3.2	Second stage of project flow	26
4.1	Initial designs geometries (a) interdigital capacitor and (b) spiral inductor	30
4.2	Graph approximation of number of fingers versus finger length	31
4.3	Effect of different designs on (a) C and (b) Q <sub>max</sub>	33

4.4	Effect of different number of fingers on (a) C and (b) $Q_{max}$	34
4.5	Effect of different finger lengths on (a) C and (b) $Q_{max}$	36
4.6	Effect of different types of metal on (a) C and (b) $Q_{max}$	37
4.7	Effect of different number of turns on (a) L and (b) $Q_{max}$	39
4.8	Effect of different line widths on (a) L and (b) $Q_{max}$	40
4.9	Effect of different metal materials on (a) L and (b) $Q_{max}$	42
4.10	The optimized configuration of C and L	43
4.11	Responses of the optimized configuration of (a) interdigital capacitor and (b) spiral inductor	44
4.12	Layouts of (a) series LC filter and (b) shunt LC filter	45
4.13	Responses of (a) series LC filter and (b) shunt LC Filter	46
4.14	Single stage series-shunt LC filter (a) layout and (b) response	47

## LIST OF SYMBOLS

$A$	-	Plate area
$A_1$	-	Interior capacitance of the finger
$A_2$	-	Two exterior capacitance of the finger
$C$	-	Capacitance
$D$	-	Separation between the plates
$F$	-	Frequency
$H$	-	Substrate height
$L$	-	Inductance
$L$	-	Finger Length
$Q$	-	Quality factor
$Q_c$	-	Quality factor due to conductor losses
$Q_d$	-	Quality factor due to dielectric losses
$Q_{\max}$	-	Maximum quality factor
$R_{DC}$	-	DC resistance
$R_s$	-	Series resistance
$s$	-	Finger spacing
$w$	-	Conductor width
$x$	-	Finger width
$Z_{11}$	-	Impedance at 1 when port 2 is open
$Z_{12}$	-	Transition impedance when port 1 is short-circuited
$Z_{21}$	-	Transition impedance when port 2 is short-circuited
$Z_{22}$	-	Impedance at 2 when port 1 is open
$\delta$	-	Metal skin depth
$\mu_0$	-	Free space permeability

$\varepsilon_r$	-	Relative dielectric constant
$\mu m$	-	Micron meter
$\Omega$	-	Unit of resistivity, Ohm
$\omega$	-	Radian frequency, rad/s
$\sigma$	-	Bulk conductivity
$\pi$	-	22/7
$\lambda$	-	Unit of wavelength

**LIST OF ABBREBRIATIONS**

C	-	Capacitor
CMOS	-	Complementary Metal Oxide Silicon
dB	-	Decibel
EM	-	Electromagnetic simulation
GaAs	-	Gallium Arsenide
GHz	-	Giga-hertz
Hz	-	Hertz
IC	-	Integrated circuit
IDC	-	Interdigital capacitor
Im	-	Imaginary
L	-	Inductor
nH	-	nano Henry
MHz	-	Mega-hertz
MIC	-	Microwave integrated circuit
MIM	-	Metal insulator metal
MMIC	-	Monolithic microwave integrated circuit
pF	-	pico Farad
Re	-	Real
RF	-	Radio frequency
SI	-	Spiral Inductor
SRF	-	Self-resonant frequency
vs	-	versus
3-D	-	Three dimension

**LIST OF APPENDICES**

<b>APPENDIX</b>	<b>TITLE</b>	<b>PAGE</b>
A	MathCAD Computations	54
B	Full Paper, Proceedings of COMET 2008	55
C	Poster Presented during COMET 2008	61
D	Full Paper, Proceedings of TOP Exhibition 2008	62
E	Poster Presented during TOP Exhibition 2008	63

# CHAPTER 1

## INTRODUCTION

The first chapter presents introductory part of thesis; project background, objective, scopes of project, and finally the organization of the thesis.

### 1.1 Project Background

Two most important circuit elements for radio frequency, RF, applications are RF inductors and capacitors. These form the basis of many RF circuits such as frequency-tuners, filters, mixers and matching networks [1]-[8]. A number of researches on the design of the on-chip components have been reported [9]-[24]. Several design configurations have been proposed. The feasibility of these elements to function as filters has been demonstrated [25]-[27]. Such feasibility is a challenging and interesting research on the lumped RF components.



## 1.2 Objective of Project

The objective of the project is to design an RF filter made of on-chip RF inductor and capacitor lumped elements. The chosen configurations are the interdigital capacitor and spiral inductor as depicted in Figures 1.1 and 1.2.

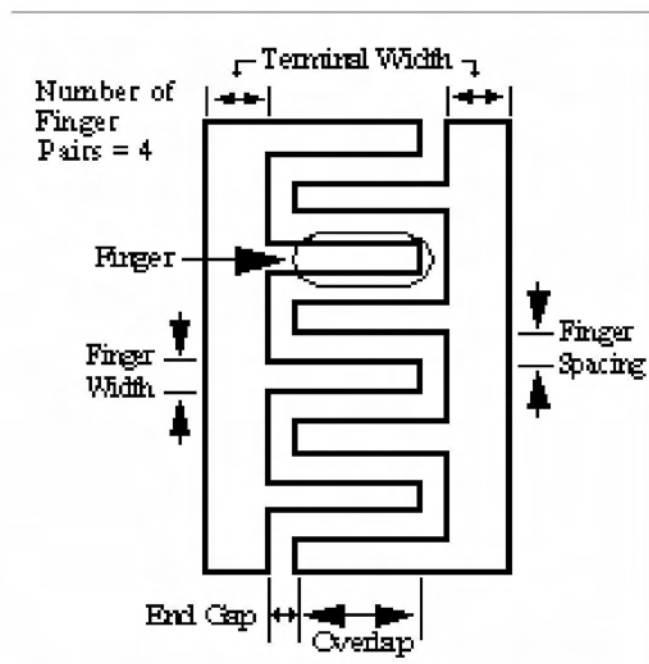


Figure 1.1: An interdigital capacitor configuration.

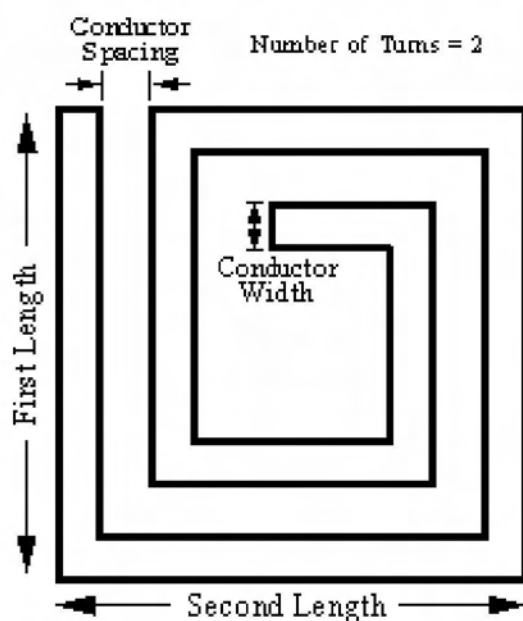


Figure 1.2: A spiral planar inductor configuration.

### **1.3 Scopes of Project**

The scopes of the project are as follows:

- (a) Optimization of the RF capacitor,  $C$ , with the highest quality factor,  $Q$ .
- (b) Optimization of the RF inductor,  $L$ , with the highest quality factor,  $Q$ .
- (c) Design of three LC filter configurations; namely, series LC filter, shunt LC filter and single-stage series-shunt LC filter.

MathCAD software [28] is used for mathematical computations while Microwave Office software [29] and SonnetLite software are used for the simulations. The computation RF lumped element components are desired to operate at 13 GHz with good return loss of below -10 dB, transmission coefficient of better than -10 dB and Q-factor of at least 65.

### **1.4 Organization of Thesis**

This thesis consists of five chapters and described as follows:

Chapter 1 presents a brief background of the project, followed by the objective, and scopes of project. The organisation of the chapters in the thesis is then briefly described.

Chapter 2 briefly described the relevant theory, along with review of related research. Formulations used in passive microwave lumped elements, i.e. capacitors and inductors, are described. It also covers the principles of RF LC filters.

In Chapter 3, the design methodology of designing the filters formed from using these two RF elements is described. It also presents the flow of the project and a brief explanation on the software used.

The results obtained are presented and analysed in Chapter 4. A summary is provided.

The final chapter concludes the thesis. Suggestions for future work are then presented

## REFERENCES

- [1] A. Glover, S.R. Pennock and P. R. Shepherd, “*Microwave Devices, Circuits and Subsystems for Communications Engineering*”, New York: Wiley, 2005.
- [2] Inder Bahl and Prakash Bhartia, “*Microwave Solid State Circuit Design*”, 2<sup>nd</sup> Edition, New York: Wiley, 2003.
- [3] Inder Bahl, “*Lumped Elements for RF and Microwave Circuit*”, Boston: Artech, 2003.
- [4] Thomas H. Lee, “*Planar Microwave Engineering*”, London: Cambridge University Press, 2004.
- [5] Kai Chang, “*RF and Microwave Wireless System*”, New York: Wiley, 2000.
- [6] D. K. Misra, “*Radio-Frequency and Microwave Communication Circuits: Analysis and Design*”, 2<sup>nd</sup> Edition, New York: Wiley, 2004.
- [7] C. A. Balanis, “*Antenna Theory, Analysis and Design*”, 3<sup>rd</sup> Edition, New York: Wiley, 2005.
- [8] D. M. Pozar, “*Microwave Engineering*”, 3<sup>rd</sup> Edition, New York: Wiley, 2005.
- [9] Nihad Dib, Qiu Zhang and Ulrich Rohde, “New CAD Model of the Microstrip Interdigital Capacitor”, *Active and Passive Electronic Components*, Vol. 27, pp. 237-245, December 2004.
- [10] Kalavathi Subramaniam, Albert Victor Kordesch and Mazlina Esa, “Design and Modeling of Metal Finger Capacitors for RF Applications”, *Asia-Pacific Conference on Applied Electromagnetics Proceedings, Malaysia*, pp. 293-296, December 2005.
- [11] Gary D. Alley, “Interdigital Capacitors and Their Application to Lumped Element Microwave Circuit”, *IEEE Transactions Microwave Theory Technique*, Vol. MTT-18, pp.1028-1033, December 1970.
- [12] Reza Esfandiari, Douglas W. Maki and Mario Siracusa, “Design of Interdigitated Capacitors and Their Application to Gallium Arsenide

- Monolithic Filters”, *IEEE Transactions of Microwave Theory and Technique*, Vol. 31, No. 1, January 1983.
- [13] C. Patrick Yue and S. Simon Wong, “Physical Modeling of Spiral Inductors on Silicon”, *IEEE Transactions on Electron Devices*, Vol. 47, No.3, March 2000.
- [14] H. M. Greenhouse, “Design of Planar Rectangular Microelectronic Inductors”, *IEEE Transactions on Parts, Hybrids and Packaging*, Vol. PHP-10, No.2, pp. 101-109, June 1974.
- [15] Mariyatul Qibtiyah Mohd Noor and Mazlina Esa, “*Design and Modeling of On-Chip Planar Capacitor for RF Application*”, Regional Postgraduate Conference on Engineering and Science (RPCES 2006), Malaysia, pp. 235-239, July 2006.
- [16] H. A. Wheeler, “Simple Inductance Formulas for Radio Coils”, *Proceedings IRE*, Vol. 16, No. 10, pp. 1398-1400, October 1928.
- [17] Sunderarajan S. Mohan, Maria del Mar Hershenson, Stephen P. Boyd and Thomas H. Lee, “Simple Accurate Expressions for Planar Spiral Inductances”, *IEEE Journal of Solid-State Circuits*, Vol. 34, No.10, October 1999.
- [18] Joachim N. Burghartz and Behzad Rejaei, “On the Design of RF Spiral Inductors on Silicon”, *IEEE Transactions on Electron Devices*, Vol. 50, No. 3, March 2003.
- [19] Joachim N. Burghartz, D. C. Edelstein, Mehmet Soyuer, H. A. Ainspan and Keith A. Jenkins, “RF Circuit Design Aspects of Spiral Inductors on Silicon”, *IEEE Journal on Solid-State Circuits*, Vol. 33, No. 12, December 1998.
- [20] James C. Rautio, “Free EM Simulator Analyzes Spiral Inductor on Silicon”, *Microwaves & RF Magazine*, pp. 165-172, September 1999.
- [21] Wanchun Tang, Yaning Zhu and Y. Leonard Chow, “Inductance Calculation of Spiral Inductors in Different Shapes”, *IEEE APMC Proceedings*, 2005.
- [22] See Guan Huei, Mazlina Esa and Albert Victor Kordesh, “RF Spiral Planar Inductor Designs – Preliminary Results”, *Asia-Pacific Conference on Applied Electromagnetics (APACE 2003)*, Malaysia, pp. 16-20, 2003.
- [23] S. J. Pan, L. W. Li and W. Y. Yin, “Performance Trends of On-Chip Spiral Inductors for RFICs”, *Progress in Electromagnetic Research, PIER 45*, pp. 123-151, 2004.

- [24] Arthur Nieuwoudt, Michael S. McCorquodale, Ruba T. Borno and Yehia Massoud, "Accurate Analytical Spiral Inductor Modeling Techniques for Efficient Design Space Exploration", *IEEE Electron Device Letters*, Vol. 27, No.12, pp. 998-1001, December 2006.
- [25] Telesphor Kamgaing, Rashaunda Henderson and Michael Petras, "Design of RF Filters Using Silicon Integrated Passive Components", *IEEE Topical Meeting on Silicon Monolithic Integrated Circuits in RF Systems*, pp. 33-36, 2004.
- [26] Alexander Mostov and Rishon Letzion, "LC Filter With Suspended Printed Inductor and Compensating Interdigital Capacitor", United States Patent, *Patent No. US 6,448,873 B1*, September 2002.
- [27] Toshimi Kaneko and Masahiko Kawaguchi, "LC Filter", United States Patent, *Patent No. 5,032,810*, July 1991.
- [28] [www.mathcad.com](http://www.mathcad.com)
- [29] [www.sonnetusa.com](http://www.sonnetusa.com)
- [30] Y.Eo and W.R. Eisenstadt, "*High Speed VLSI Interconnect Modeling Based on S-Parameter Measurements*", SRC Publication C93337, July 1993.